

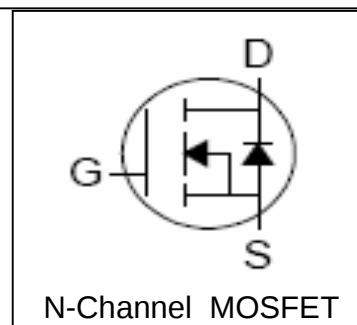
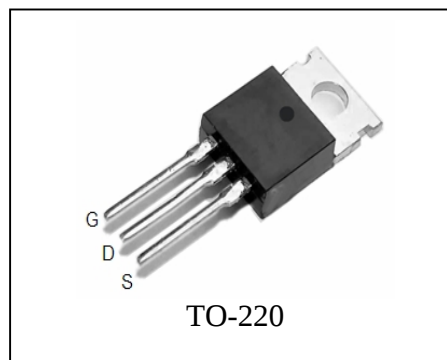
Features

- 500V/8A,
 $R_{DS(ON)} = 0.7\Omega$ (Typ.) @ $V_{GS} = 10V$
- Gate charge minimized
- Low C_{rss} (Typ. 26pF)
- Extremely high dv/dt capability
- 100% avalanche tested
- Lead Free and Green Available

Applications

- High efficiency switch mode power supplies
- Lighting

Pin Description



Absolute Maximum Ratings

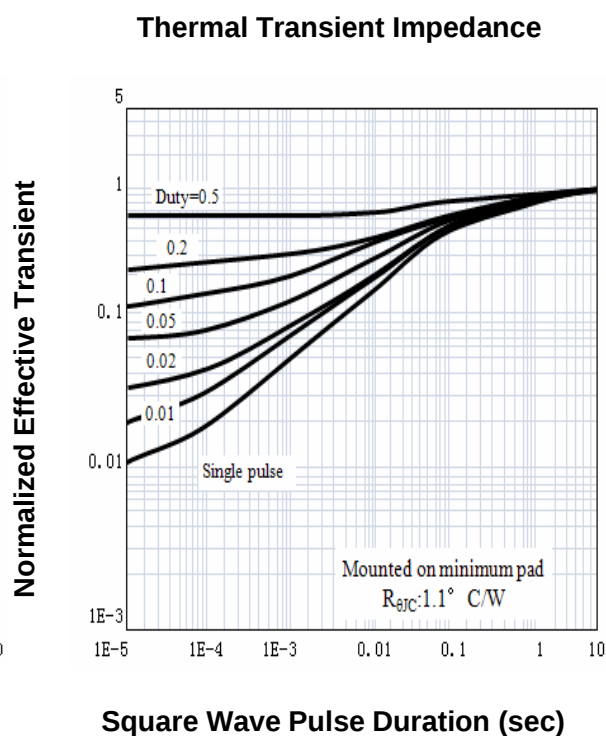
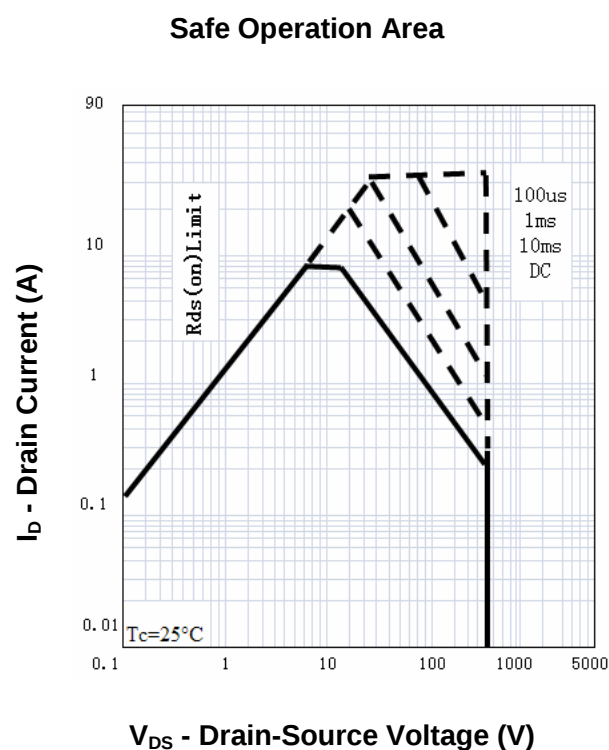
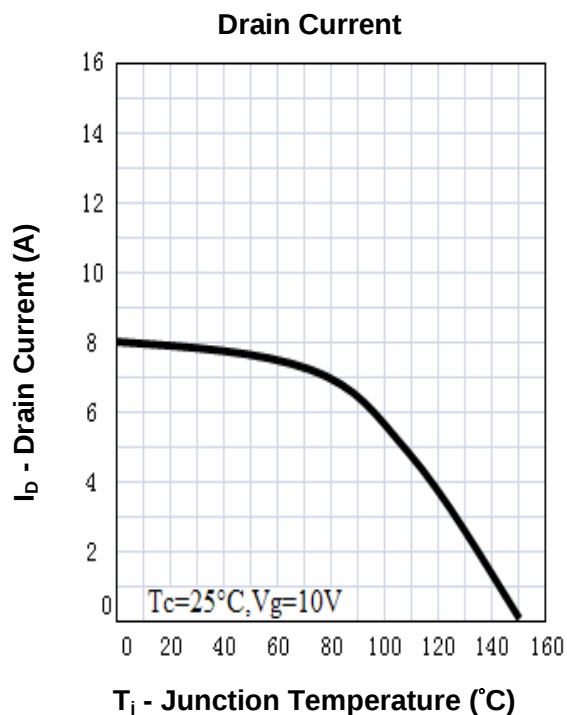
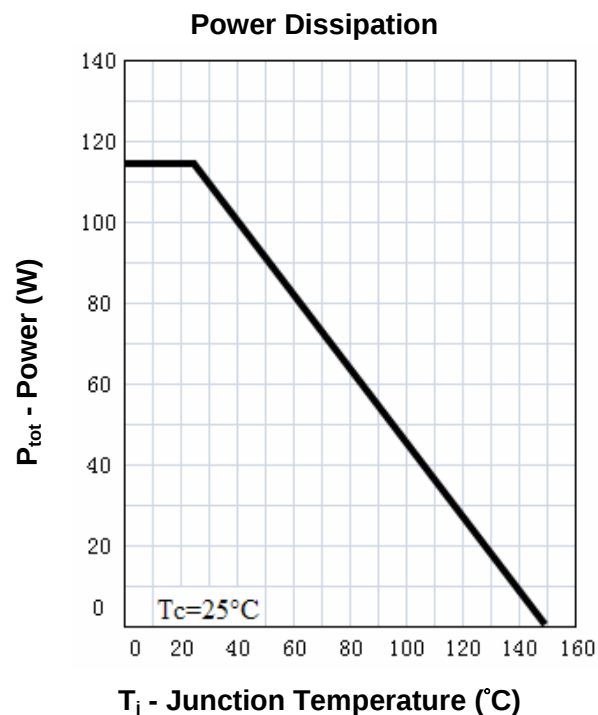
Symbol	Parameter		Rating	Unit
Common Ratings (T _C =25°C Unless Otherwise Noted)				
V _{DSS}	Drain-Source Voltage		500	V
V _{GSS}	Gate-Source Voltage		±30	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	°C
I _S	Diode Continuous Forward Current	T _C =25°C	8	A
Mounted on Large Heat Sink				
I _{DP}	300μs Pulse Drain Current Tested	T _C =25°C	32 ^①	A
I _D	Continuous Drain Current	T _C =25°C	8 ^①	A
		T _C =100°C	5.6 ^①	
P _D	Maximum Power Dissipation	T _C =25°C	114	W
		T _C =100°C	45	
R _{θJC}	Thermal Resistance-Junction to Case		1.1	°C/W
Drain-Source Avalanche Ratings				
E _{AS} ^②	Avalanche Energy, Single Pulsed		78	mJ

Electrical Characteristics (T_C=25°C Unless Otherwise Noted)

Symbol	Parameter	Test Condition	RU5H8R			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	500			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 500V, V _{GS} =0V			1	μA
		T _J =85°C			30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±30V, V _{DS} =0V			±100	nA
R _{DS(ON)} ^③	Drain-Source On-state Resistance	V _{GS} = 10V, I _{DS} =4A		0.7	0.85	Ω
Diode Characteristics						
V _{SD} ^③	Diode Forward Voltage	I _{SD} =8A, V _{GS} =0V			1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =8A, dI _{SD} /dt=100A/μs		310		ns
Q _{rr}	Reverse Recovery Charge			2.3		μC
Dynamic Characteristics ^④						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz		10		Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} = 250V, Frequency=1.0MHz		1110		pF
C _{oss}	Output Capacitance			195		
C _{rss}	Reverse Transfer Capacitance			26		
t _{d(ON)}	Turn-on Delay Time	V _{DD} =250V, R _L =32Ω, I _{DS} =8A, V _{GEN} = 10V, R _G =25Ω		30		ns
t _r	Turn-on Rise Time			50		
t _{d(OFF)}	Turn-off Delay Time			120		
t _f	Turn-off Fall Time			50		
Gate Charge Characteristics ^④						
Q _g	Total Gate Charge	V _{DS} =400V, V _{GS} = 10V, I _{DS} =8A		25		nC
Q _{gs}	Gate-Source Charge			4		
Q _{gd}	Gate-Drain Charge			10		

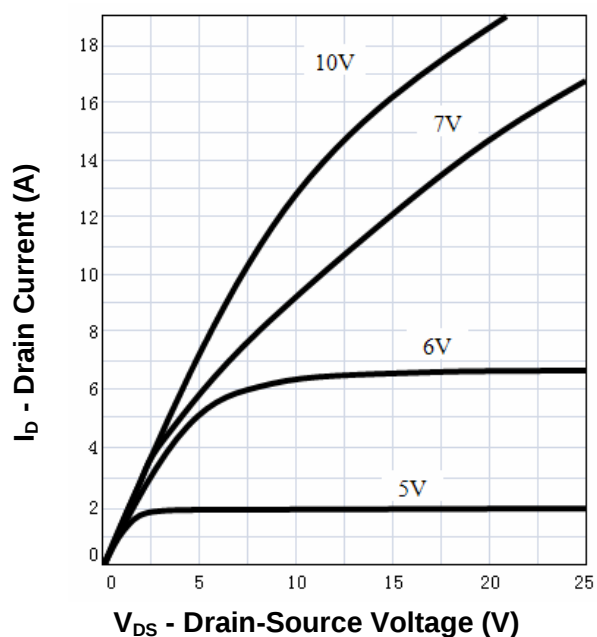
- Notes: ① Current limited by maximum junction temperature.
 ② Limited by T_{Jmax}, I_{AS} =12.5A, V_{DD} = 100V, R_G = 50Ω , Starting T_J = 25°C.
 ③ Pulse test ; Pulse width≤300μs, duty cycle≤2%.
 ④ Guaranteed by design, not subject to production testing.

Typical Characteristics

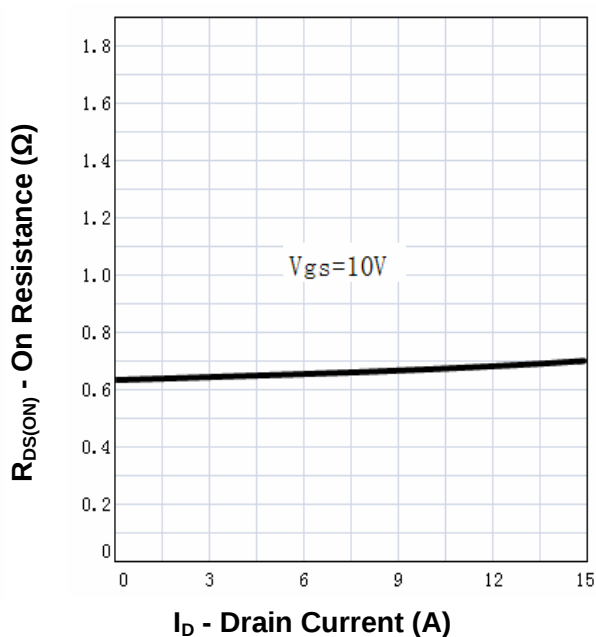


Typical Characteristics

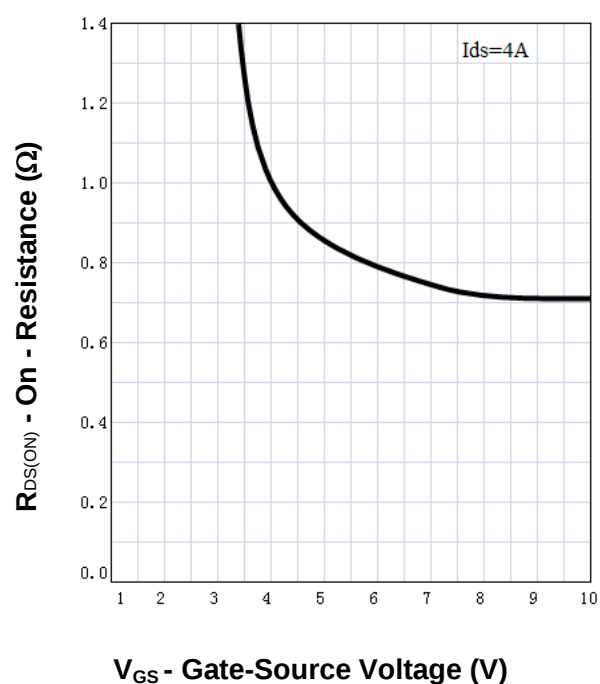
Output Characteristics



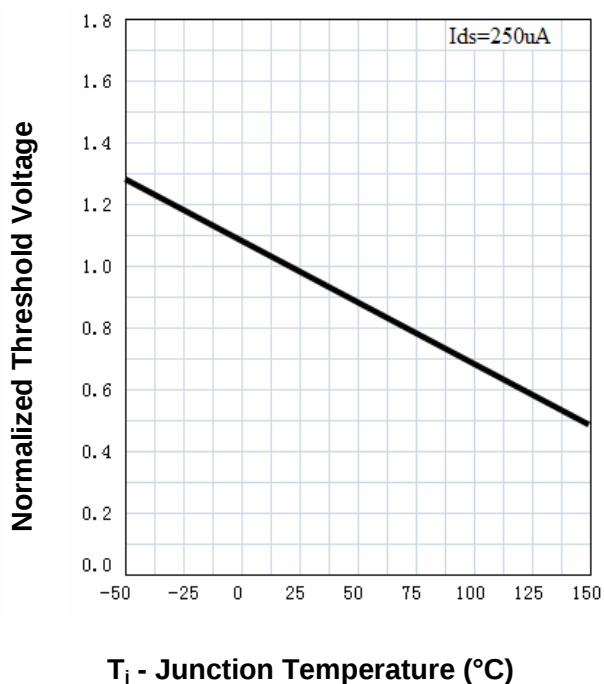
Drain-Source On Resistance



Drain-Source On Resistance

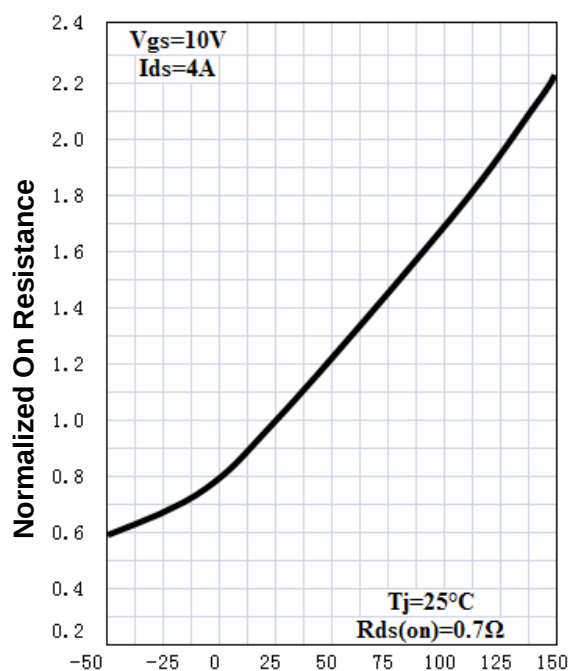


Gate Threshold Voltage



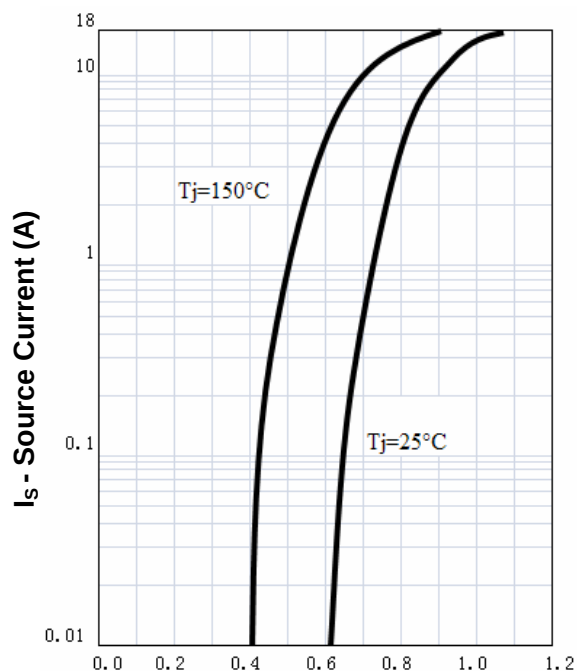
Typical Characteristics

Drain-Source On Resistance



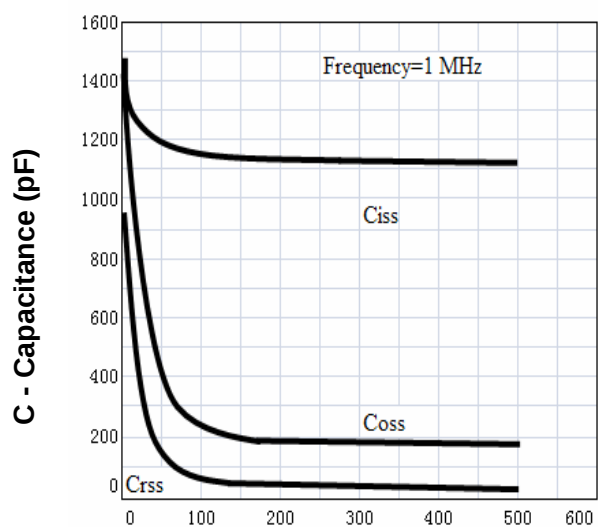
T_j - Junction Temperature ($^{\circ}\text{C}$)

Source-Drain Diode Forward



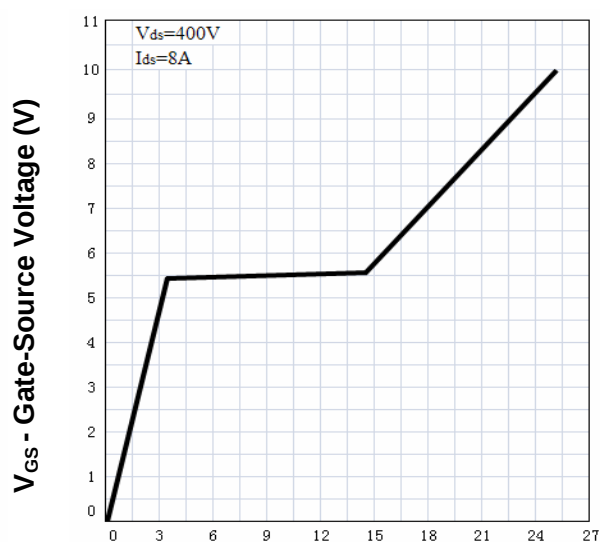
V_{SD} - Source-Drain Voltage (V)

Capacitance



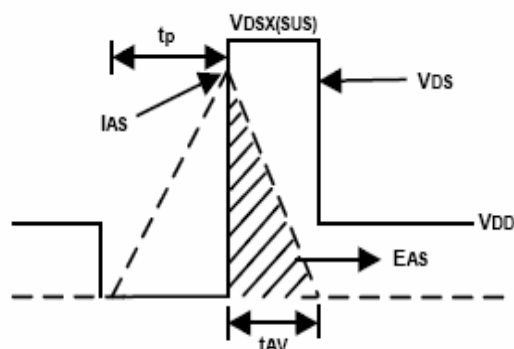
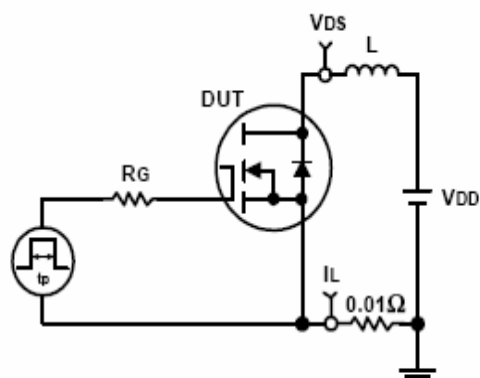
V_{DS} - Drain-Source Voltage (V)

Gate Charge

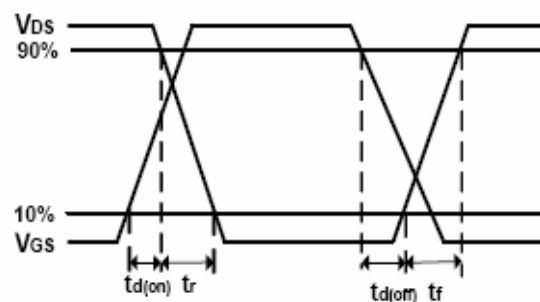
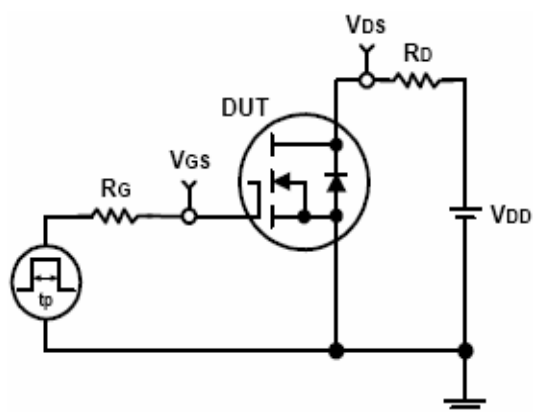


Q_G - Gate Charge (nC)

Avalanche Test Circuit and Waveforms



Switching Time Test Circuit and Waveforms

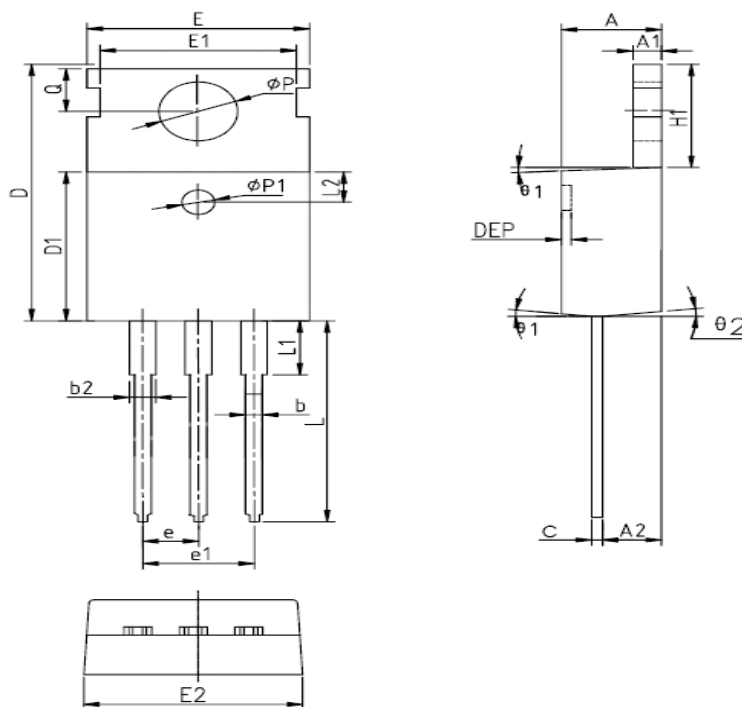


Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU5H8R	RU5H8R	TO-220	Tube	50	-	-

Package Information

TO-220FB-3L



SYMBOL	MM			INCH			SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX		MIN	NOM	MAX	MIN	NOM	MAX
E	9.96	10.16	10.36	0.392	0.400	0.408	$\phi p3$	-	3.450	-	-	0.136	-
A	4.50	4.70	4.90	0.177	0.185	0.193	$\theta 1$	5°	7°	9°	5°	7°	9°
A1	2.34	2.54	2.74	0.092	0.100	0.108	$\theta 2$	-	45°	-	-	45°	-
A2	0.95	1.05	1.15	0.037	0.041	0.045	DEP	0.05	0.10	0.15	0.002	0.004	0.006
A3	0.42	0.52	0.62	0.017	0.020	0.024	F1	1.90	2.00	2.10	0.075	0.079	0.083
A4	2.65	2.75	2.85	0.104	0.108	0.112	F2	13.61	13.81	14.01	0.536	0.544	0.552
c	-	0.50	-	-	0.020	-	F3	3.20	3.30	3.40	0.126	0.130	0.134
D	15.67	15.87	16.07	0.617	0.625	0.633	G	3.25	3.45	3.65	0.128	0.136	0.144
Q	8.80	9.00	9.20	0.346	0.354	0.362	G1	5.90	6.00	6.10	0.232	0.236	0.240
H1	6.48	6.68	6.88	0.255	0.263	0.271	G2	6.90	7.00	7.10	0.272	0.276	0.280
e	2.54BSC			0.1BSC			b1	1.17	1.20	1.24	0.046	0.047	0.048
ϕp	-	3.183	-	-	0.125	-	b2	0.77	0.8	0.85	0.030	0.031	0.033
L	12.78	12.98	13.18	0.503	0.511	0.519	b3	1.10	1.30	1.50	0.043	0.051	0.059
D1	8.99	9.19	9.39	0.354	0.362	0.370	E1	9.8	10.00	10.20	0.386	0.394	0.412
$\phi p1$	1.40	1.50	1.60	0.055	0.059	0.063	K1	0.75	0.8	0.85	0.030	0.031	0.033
$\phi p2$	1.15	1.20	1.25	0.045	0.047	0.049							

ALL DIMENSIONS REFER TO JEDEC STANDARD
DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS

Customer Service

Worldwide Sales and Service:

Sales@ruichips.com

Technical Support:

Technical@ruichips.com

Investor Relations Contacts:

Investor@ruichips.com

Marcom Contact:

Marcom@ruichips.com

Editorial Contact:

Editorial@ruichips.com

HR Contact:

HR@ruichips.com

Legal Contact:

Legal@ruichips.com

Shen Zhen RUICHIPS Semiconductor CO., LTD

Room 501, the 5floor An Tong Industrial Building,
NO.207 Mei Hua Road Fu Tian Area Shen Zhen City, CHINA

TEL: (86-755) 8311-5334

FAX: (86-755) 8311-4278

E-mail: Sales-SZ@ruichips.com